

POWER

TO DO ANYTHING

Your ultimate power resource

AC-to-Processor: Powering Tomorrow's Datacenters with TI GaN

March 27-29, 2017

For questions please contact masoud@ti.com

SLYT717

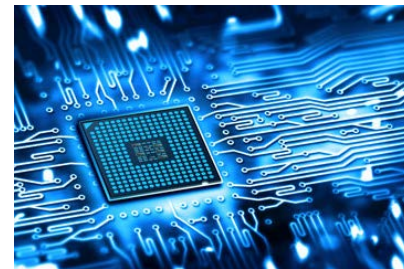
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AC-to-Processor at Over 2X the Power Density

- TI GaN enables **>2X power density improvements from AC to point-of load**, by **solutions** that are:
 - **Cooler:** 99% Efficient Totem Pole PFC scalable to 3kW
 - **Faster:** 1MHz - 140W/in³ isolated DC/DC LLC converter
 - **Smaller:** 2x75A stackable, single-stage 48V-to-POL solution
 - **Easier:** Industry most integrated GaN with the largest ecosystem and solution footprint



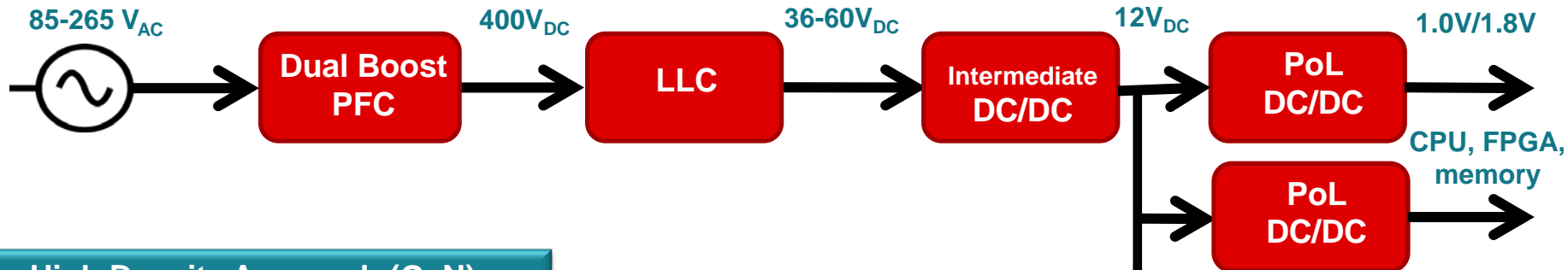
Do More
With Less Power



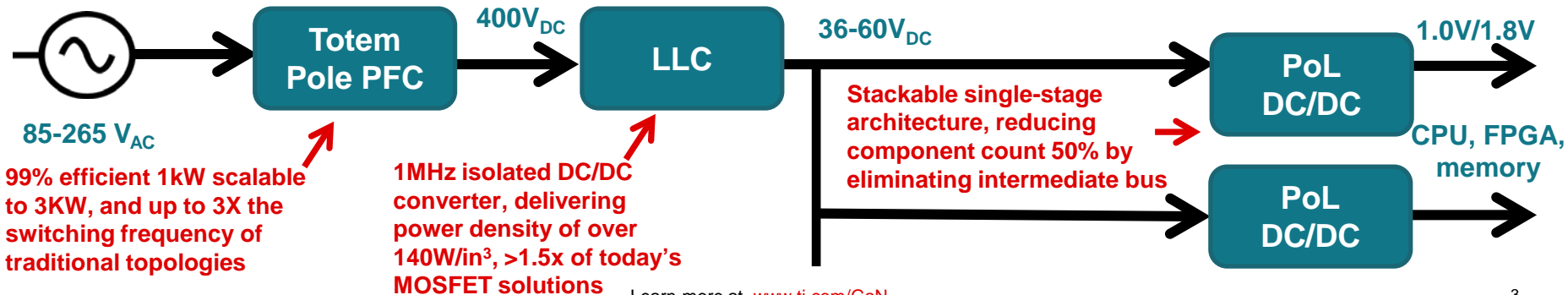
Learn more at www.ti.com/GaN

TI GaN: Rethink your AC to PoL Power Design

Current Solution (MOSFET)

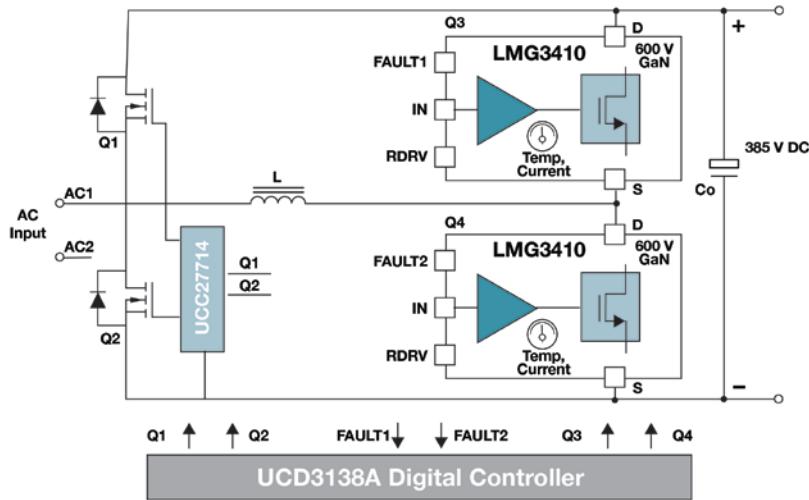


High Density Approach (GaN)



Learn more at www.ti.com/GaN

PFC Solution: 1kW 140kHz Totem-Pole CCM



Increase Density by 2X to 125 w/in³

Excludes EMI

Specifications

- Continuous Conduction Mode PFC
- Universal AC line input
- 385V DC bus output
- 1 kW output across universal input

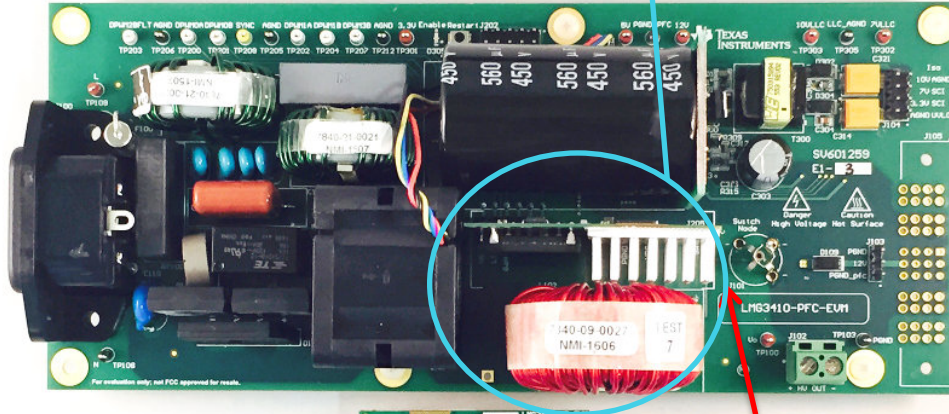
Features

- LMG3410 GaN FET implemented with LMG3410-HB-EVM
- Highly integrated UCD3138A digital solution offering superior performance
- Advanced control algorithm
- Adaptive dead time control
- Excellent THD and PF

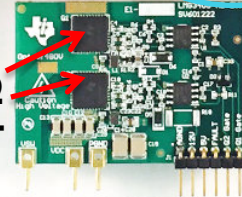
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PFC Solution: 1kW 140kHz Totem-Pole CCM

Power Stage and Inductor



LMG3410 600V 70 mΩ
8 mm x 8 mm GaN FET

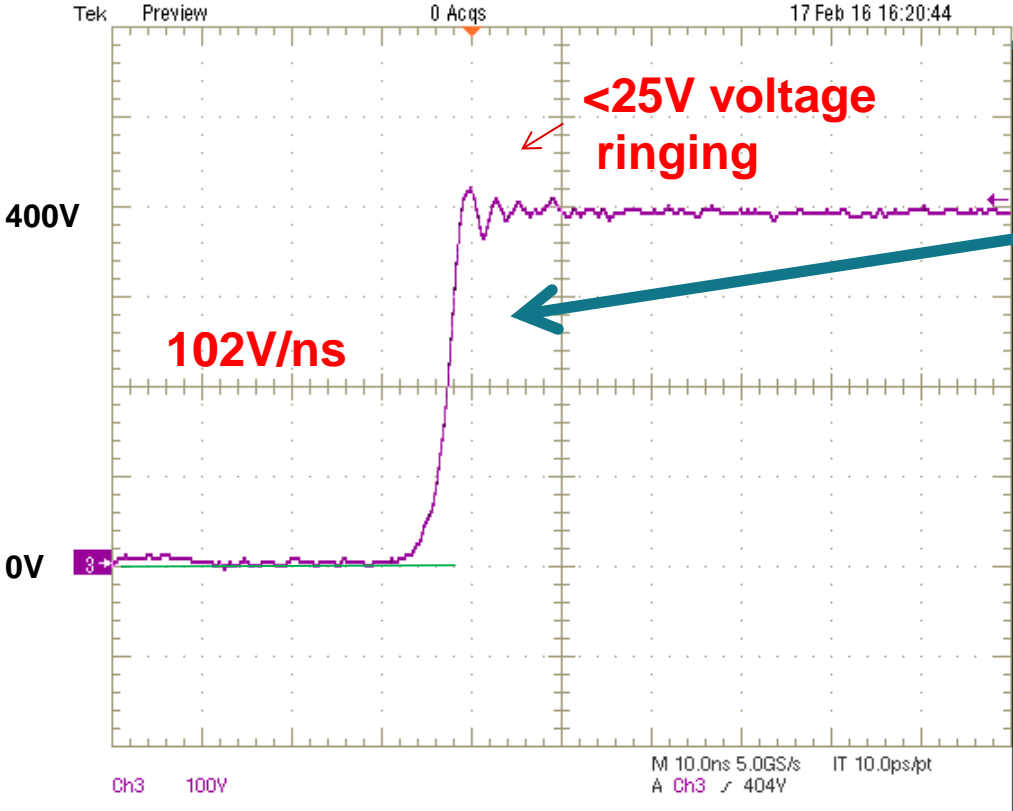


GaN FET
Daughter Card
LMG3410-HB-EVM



Learn more at www.ti.com/GaN

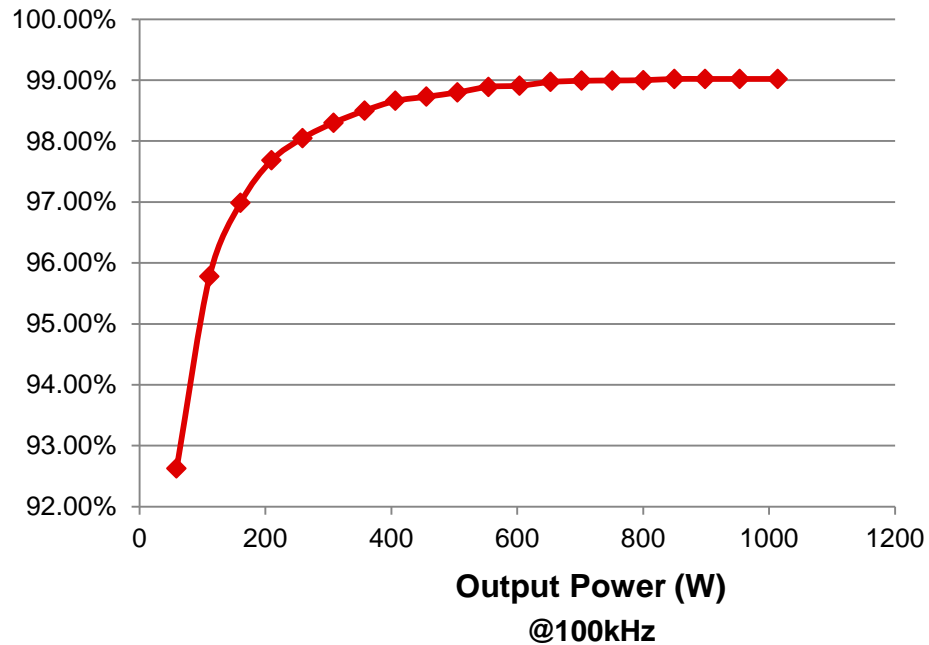
PFC Solution: Switching Node Waveform



Zero to 400V in 4ns
With TI-GaN

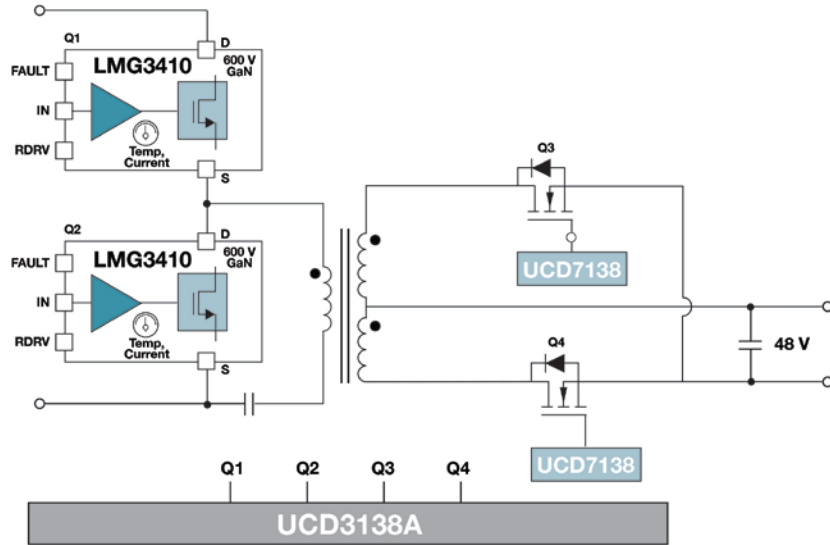
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PFC Solution: Efficiency



Learn more at www.ti.com/GaN

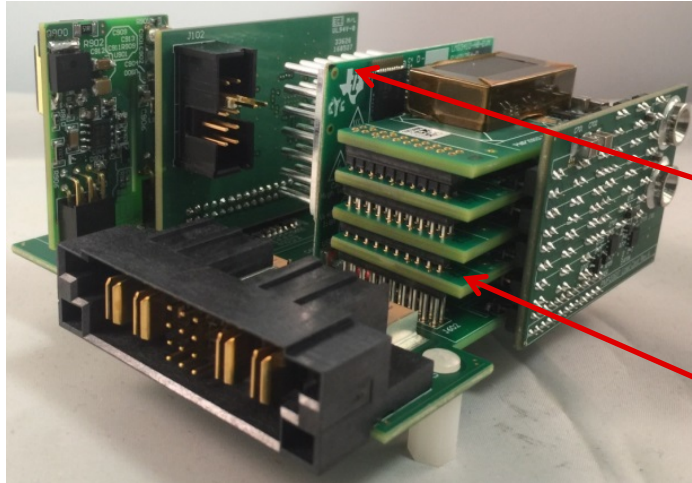
LLC Solution: 1MHz Isolated DC/DC Converter



	Specification
Input voltage (V)	380 ~ 400
Output voltage (V)	48V Nom unregulated
Power (W)	1000
Size (in)	2 x 2.1 x 1.7
Power density (W/in ³)	140 High power density
Efficiency	>97% High Efficiency
Switching frequency	1 MHz

Increase Density by 1.5X to 140 w/in³

LLC Solution: 1MHz Isolated DC/DC Converter



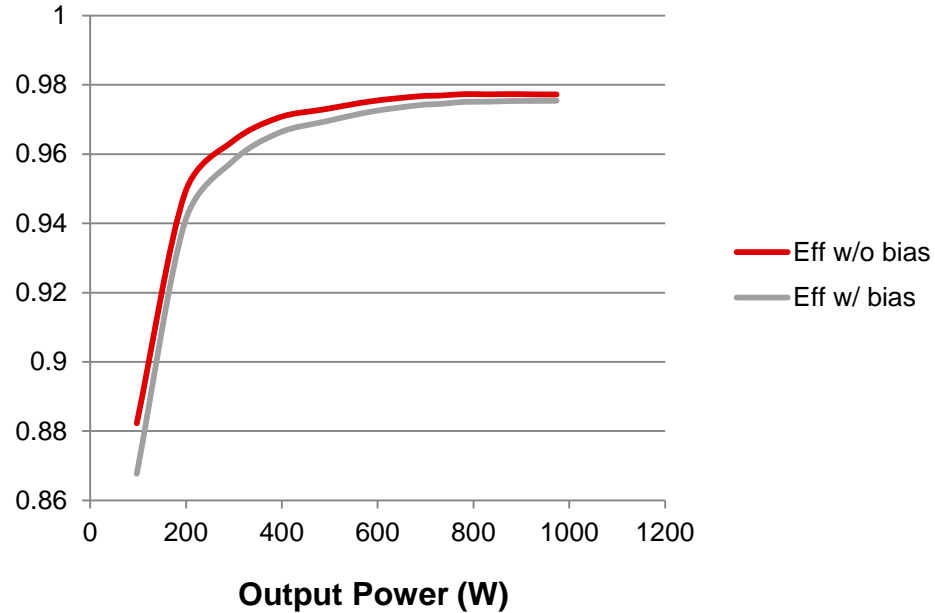
**LMG3410
Half bridge**

**Integrated
Transformer**

Learn more at www.ti.com/GaN

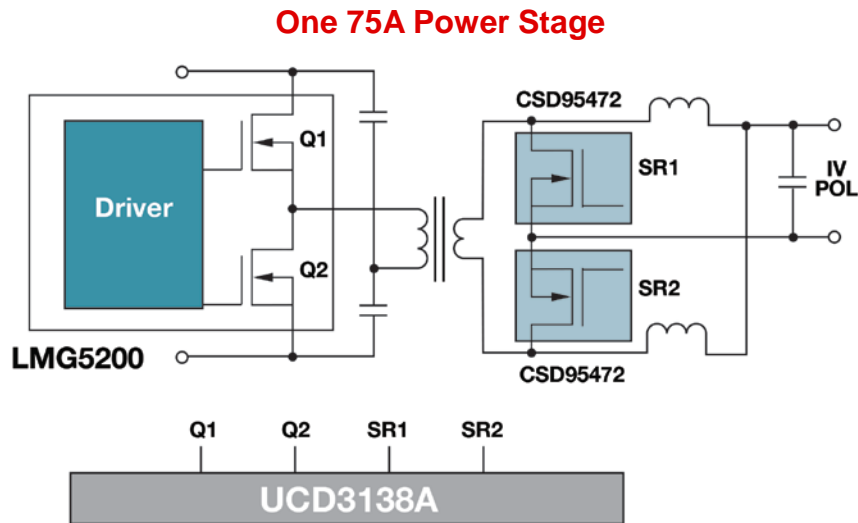
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LLC Solution: Efficiency



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48V-to-POL: 2x75A Stackable Single-Stage Solution

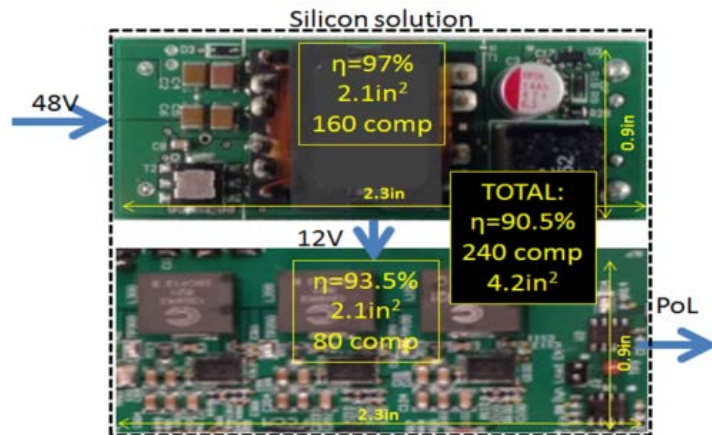


Increase Density by 4X to 160 w/in³

Single vs Two-Stage Solution:

- GaN enables an efficient hard-switched converters at higher voltages
- The [LMG5200](#) is ideal for single-stage power conversion. Applications include server and telecom POL, as well wide Vin industrial power supplies
- The single conversion reduces component count in half, and increases power density by 4X

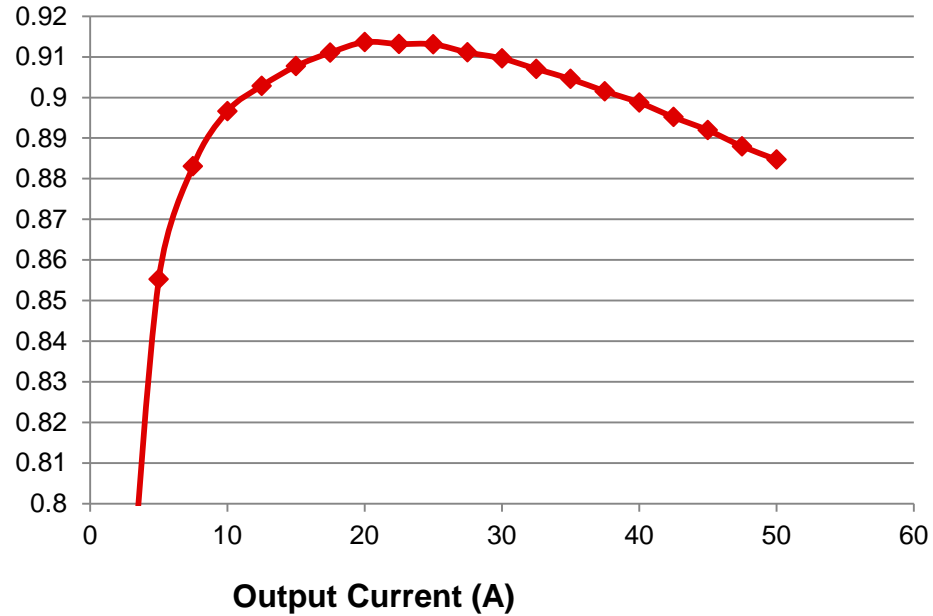
48V-to-PoL: 2x75A Stackable Single-Stage Solution



Eliminate the Intermediate
Bus Converter (IBC)

Learn more at www.ti.com/GaN

48V-to-POL: Efficiency



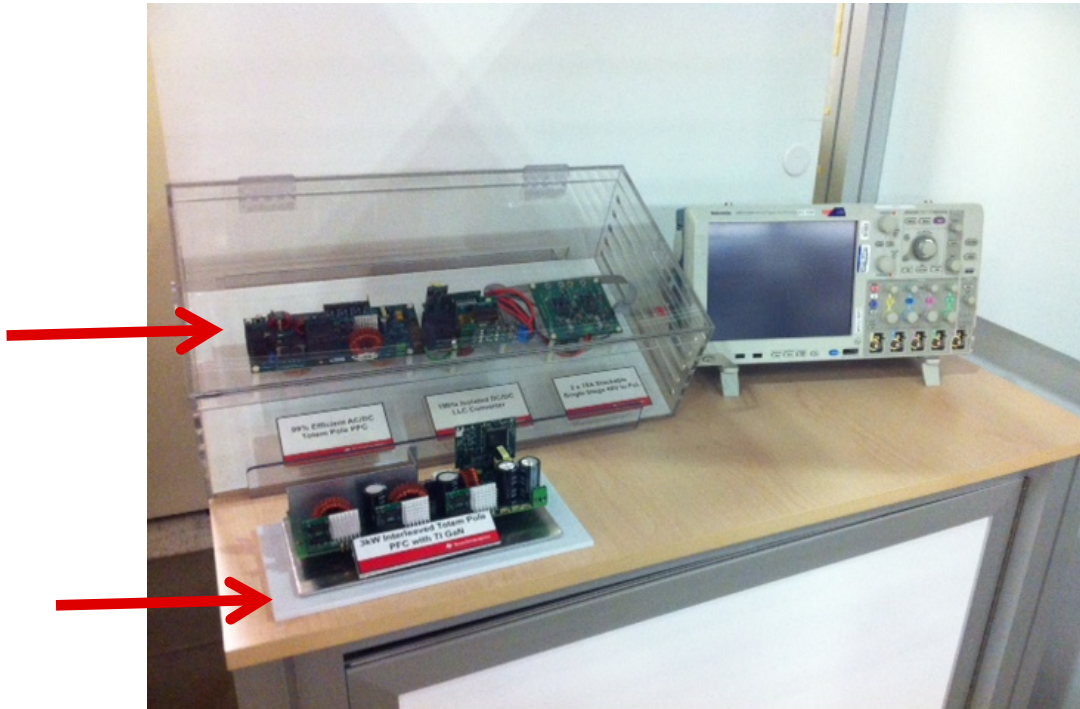
Learn more at www.ti.com/GaN

AC-to-Processor :

Powering Tomorrow's Datacenters with TI GaN

1kW PFC,
LLC,
48:POL

3kW PFC
(static)



Learn more at www.ti.com/GaN

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Product Information

LMG3410: 600 V GaN Power Stage

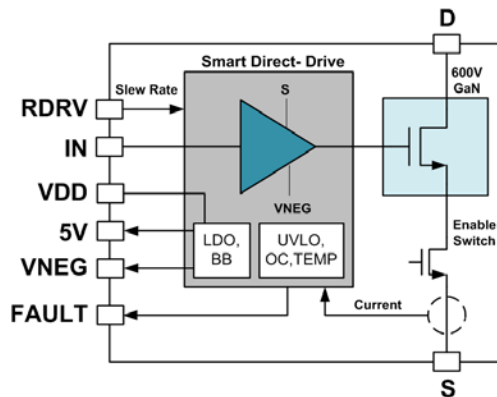
Features

- 70mΩ RDSon Drain to Source
- Integrated GaN Gate Driver
 - TI Direct-Drive technology switches the GaN directly
 - Internal buck-boost generates negative drive voltage
 - Only single +12V unregulated supply needed
 - 5V LDO to power external isolator
- External resistor sets drive strength (RDRV pin)
 - 30 V/ns to 100 V/ns adjustability
 - No compromise in gate-drive inductance
- Fault monitoring and protection
 - UVLO protection
 - Over-current protection (20nS)
 - Over-temperature protection
- SPICE model and EVM at [ti.com](https://www.ti.com)
- Package: 8 x 8 mm QFN

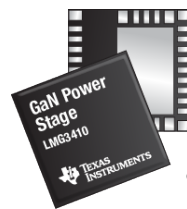
Applications

- AC rectifier to 12V/48V
- High-voltage DC distribution in server/telecom
- Photo-voltaic inverters

Functional Block Diagram



Packaging



8mm x 8mm QFN

Learn more at www.ti.com/GaN

LMG5200: 80 V/10 A GaN Half-Bridge Power Stage

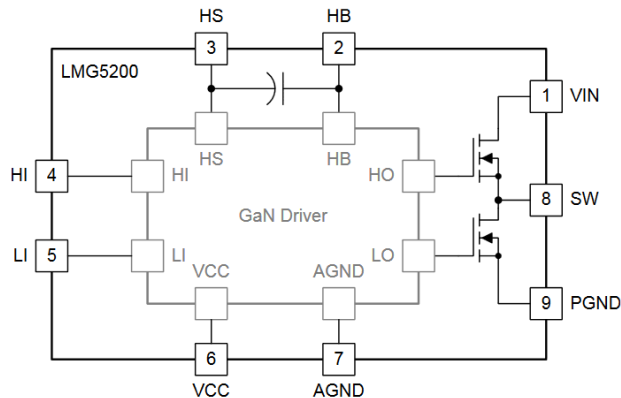
Features

- 80-V 18 m Ω devices for 10 A DC operation
- Integrated High-side and Low-side GaN driver and FETs
- Internal bootstrap supply voltage clamping to prevent GaN FET overdrive (5.2 V)
- Fast Propagation delay (25 ns)
- Excellent HS and LS matching (2 ns)
- Package: 6 x 8 mm QFN
- SPICE model at [ti.com](https://www.ti.com)
- EVM available at [ti.com](https://www.ti.com)

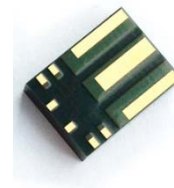
Applications

- High speed synchronous buck converters
- Wide V_{IN} to point-of-load single step converters
- Isolated DC/DC
- Class D Audio Amp
- 48-V Motor drive

Block Diagram

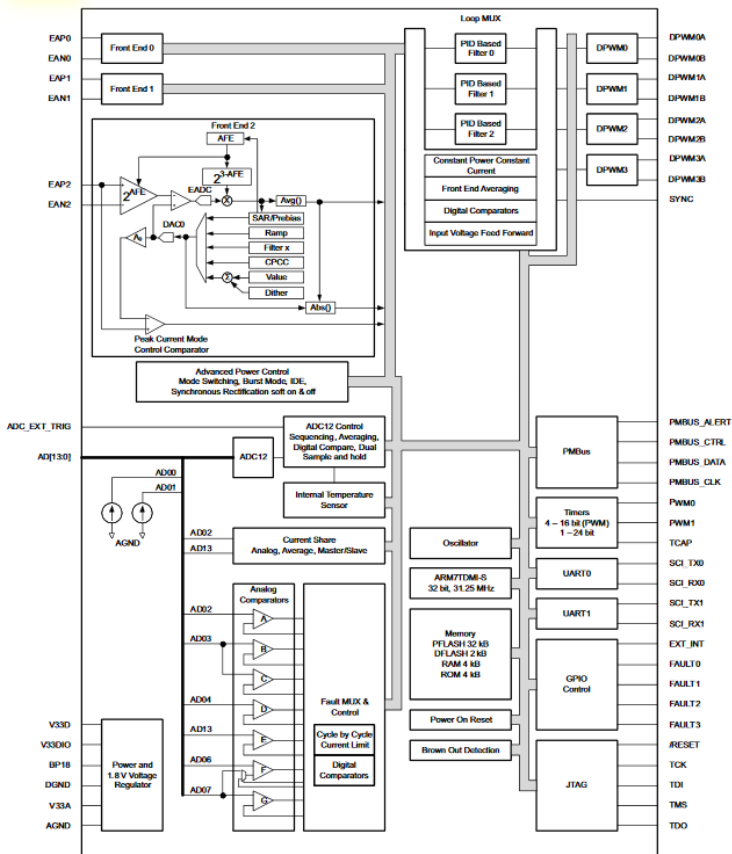


Packaging



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UCD3138: Advanced Digital Power Controller



Key Features

- 3 Independent, Multi-Nestable Feedback Loops
 - 16MHz Error Analog to Digital Converter (EADC)
 - 14-bit (effective) DAC for control loop reference
 - Dedicated PID hardware, 2p/2z configurable
 - 8 High Resolution DPWM Outputs with Leading, Trailing or Dual Edge (Triangular) Modulation
 - 4ns Freq resolution, 250ps Pulse Width resolution
 - 2MHz Max Switching Frequency
-
- High-Performance 31.25MHz, 32-bit ARM7 Processor
 - On-Chip Program & Data Flash, RAM and ROM
 - 14 Channel, 12-bit, 267ksps general purpose ADC
 - 2 UART's + PMBus Interface + JTAG Debug port
 - 7 50ns Analog Comparators, Cycle-by-cycle I_{LIMIT}
 - On-chip (BOD / POR), Single Supply Operation (3.3V)
 - External Interrupt + Fault Input & Output
 - Bootload using ROM (PMBUS) and Program Flash (UART)
-
- Configurable Feedback Control
 - Voltage Mode
 - Average Current Mode
 - Peak Current Mode with slope compensation and programmable blanking time
 - Constant Current, Constant Power
-
- Configurable Modulation Methods
 - Multiple Light Load Efficiency Modes
 - Integrated Copper Trace Current Sensing
-
- -40° C to +125° C Extended Temp Range
 - 64pin and 40pin QFN packages

Learn more at www.ti.com/GaN

- White papers
- Applications notes
- Device samples and EVM
- Spice models
- Online “E2E” community forums

Gallium Nitride (GaN) Solutions

Realize world-class power density with reliable, integrated, easy-to-use GaN solutions from TI.



GaN FET modules



Integrating GaN FETs and drivers into one, easy to use package.

GaN FET drivers



Award-winning high-speed gate drivers enabling high power density and design simplicity, available in single and dual channel low-side as well as high-side/low-side configurations.

GaN FET controllers



Analog and digital controllers easily pair with GaN products to enable a variety of high frequency applications.

Learn more at www.ti.com/GaN

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